

# 2SA1190

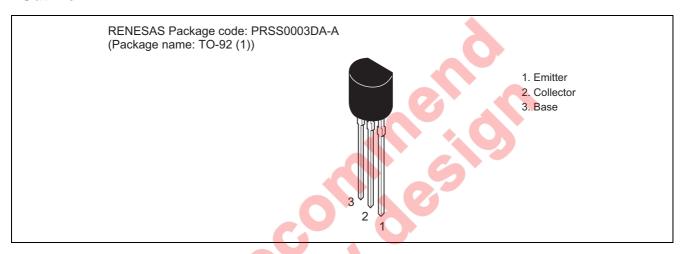
## Silicon PNP Epitaxial

REJ03G0640-0200 (Previous ADE-208-1012) Rev.2.00 Aug.10.2005

#### **Application**

- Low frequency low noise amplifier
- Complementary pair with 2SC2855 and 2SC2856

#### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Rating	Unit
Collector to base voltage	V <sub>CBO</sub>	-90	V
Collector to emitter voltage	V <sub>CEO</sub>	-90	V
Emitter to base voltage	V <sub>EBO</sub>	<b>-</b> 5	V
Collector current	Ic	-100	mA
Emitter current	Ι <sub>Ε</sub>	100	mA
Collector power dissipation	P <sub>C</sub>	400	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

#### **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

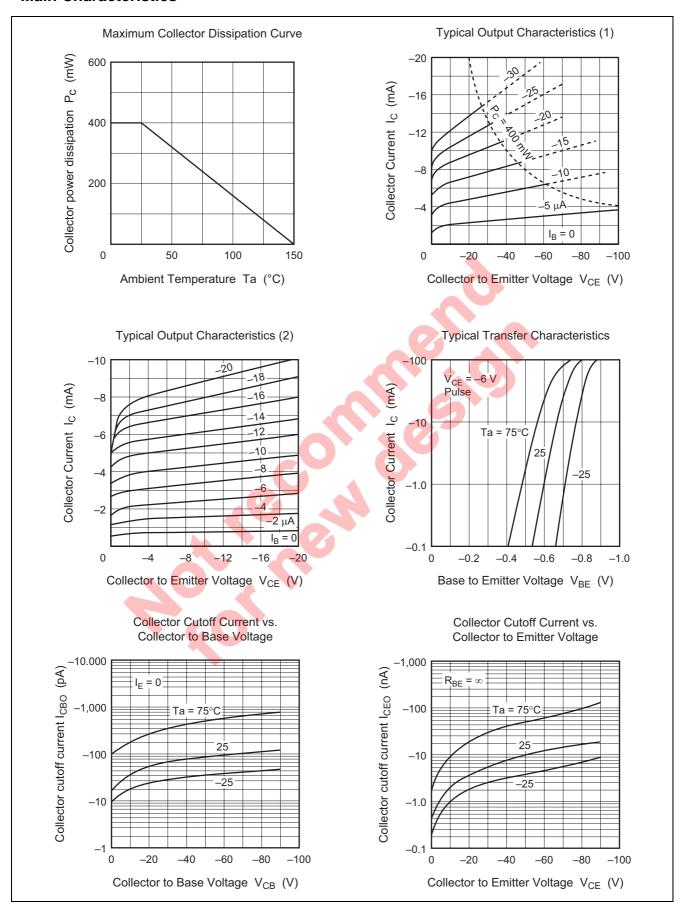
			2SA1190	)		
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	-90	_	_	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	-90	_	_	V	I <sub>C</sub> = −1 mA, R <sub>BE</sub> = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	<b>-</b> 5	_	_	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	-0.1	μΑ	$V_{CB} = -70 \text{ V}, I_{E} = 0$
Emitter cutoff current	I <sub>EBO</sub>	_	_	-0.1	μΑ	$V_{EB} = -2 \text{ V}, I_C = 0$
DC current trnsfer ratio	h <sub>FE</sub> *1	250	_	800		$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA*}^{2}$
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	_	-0.05	-0.15	V	$I_C = -10 \text{ mA},$ $I_B = -1 \text{ mA*}^2$
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	_	-0.7	-1.0	V	
Gain bandwidth product	f⊤	_	130	_	MHz	$V_{CE} = -6 \text{ V},$ $I_C = -10 \text{ mA}$
Collector output capacitance	Cob	_	3.2	_	pF	$V_{CB} = -10 \text{ V}, I_E = 0,$ f = 1 MHz
Noise figure	NF	_	0.15	1.5	dB	$V_{CE} = -6 \text{ V},$ $I_{C} = -0.1 \text{ mA},$ $R_{g} = 10 \text{ k}\Omega$ $f = 1 \text{ kHz}$
		_	0.2	2.0	dB	$V_{CE} = -6 \text{ V},$ $I_{C} = -0.1 \text{ mA},$ $R_{g} = 10 \text{ k}\Omega$ $f = 10 \text{ Hz}$
Noise voltage referred to input	en		0.7		nV/ √Hz	$V_{CB} = -6 \text{ V},$ $I_{C} = -10 \text{ mA},$ $Rg = 0, f = 1 \text{ kHz}$

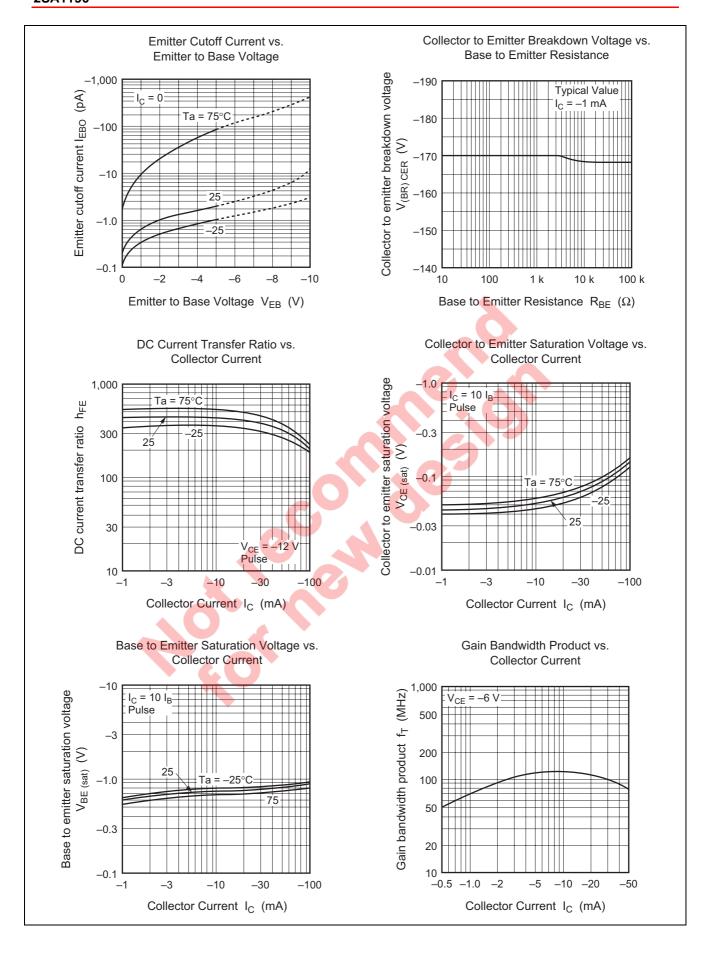
Notes: 1. The 2SA1190 and 2SA1191 are grouped by hee as follows.

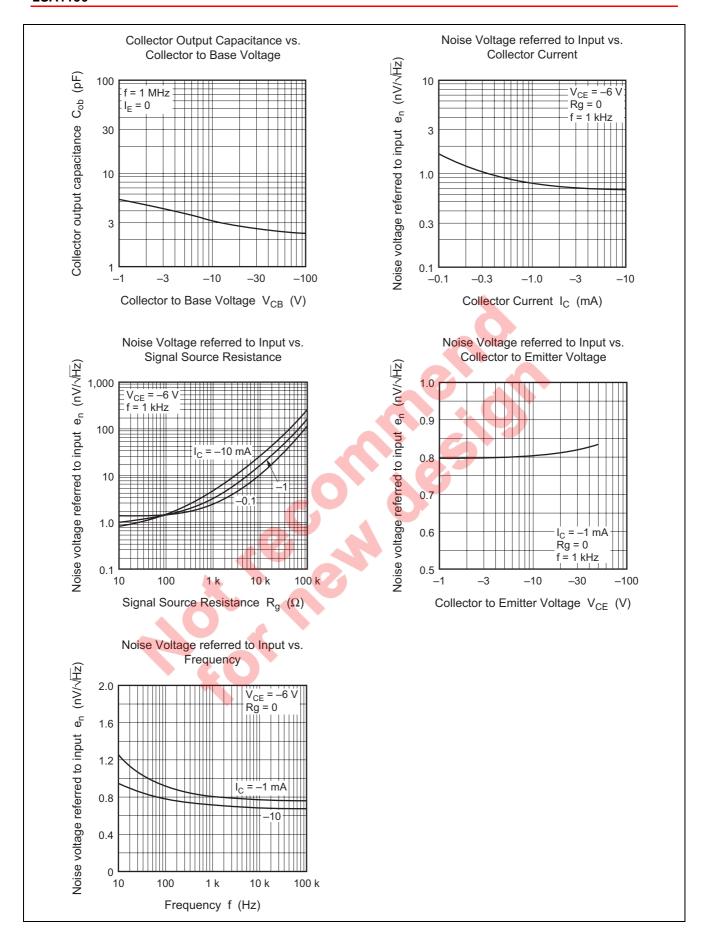
2. Pulse test

D	Е
250 to 500	400 to 800

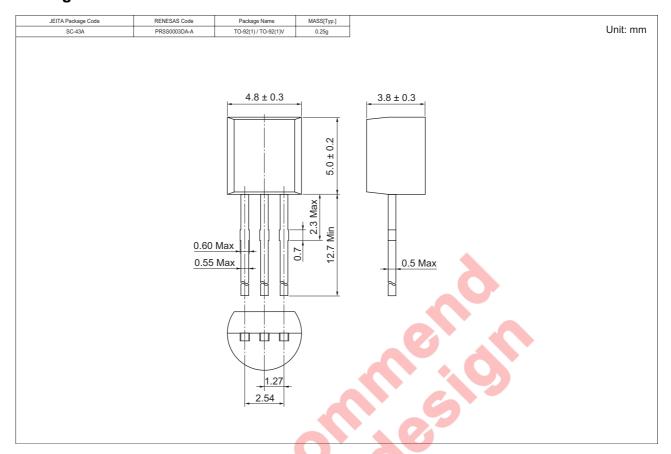
#### **Main Characteristics**







### **Package Dimensions**



### **Ordering Information**

Part Name	Quantity	Shipping Container
2SA1190DTZ-E	2500	Hold Box, Radial Taping
2SA1190ETZ-E		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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